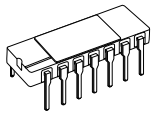
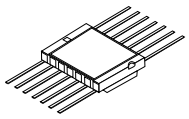
M54HC30

RAD-HARD 8-INPUT NAND GATE

- HIGH SPEED:
  t_{PD} = 13ns (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION:
  I_{CC} = 1µA(MAX.) at T_A=25°C
- HIGH NOISE IMMUNITY:
  $V_{NIH} = V_{NIL}$ = 28% V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:
  $|I_{OH}| = I_{OL}$ = 4mA (MIN)
- BALANCED PROPAGATION DELAYS:
  $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
  V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 54 SERIES 30
- SPACE GRADE-1: ESA SCC QUALIFIED
- 50 krad QUALIFIED, 100 krad AVAILABLE ON REQUEST
- NO SEL UNDER HIGH LET HEAVY IONS IRRADIATION
- DEVICE FULLY COMPLIANT WITH SCC-9201-110



DILC-14



FPC-14

ORDER CODES

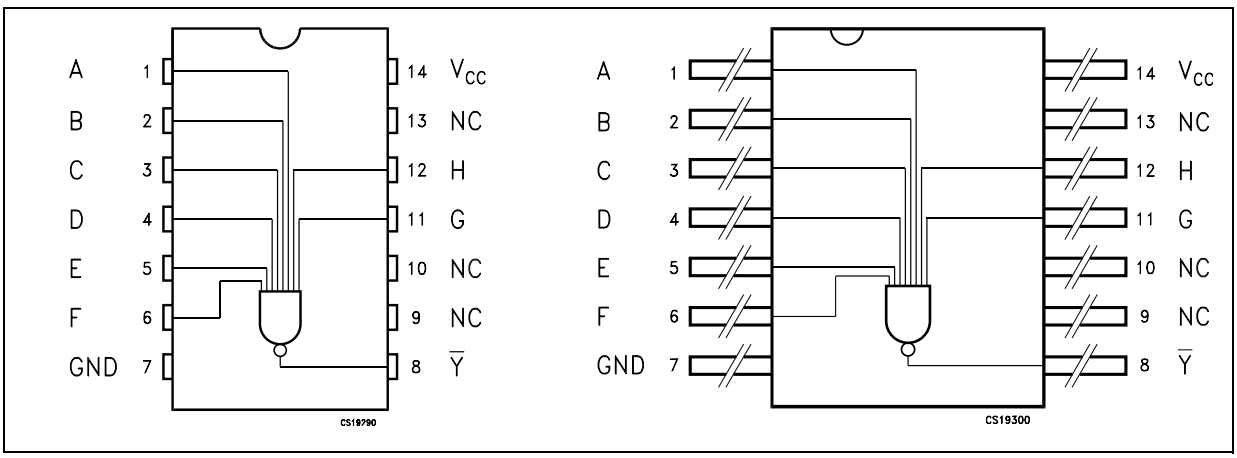
PACKAGE	FM	EM
DILC	M54HC30D	M54HC30D1
FPC	M54HC30K	M54HC30K1

DESCRIPTION

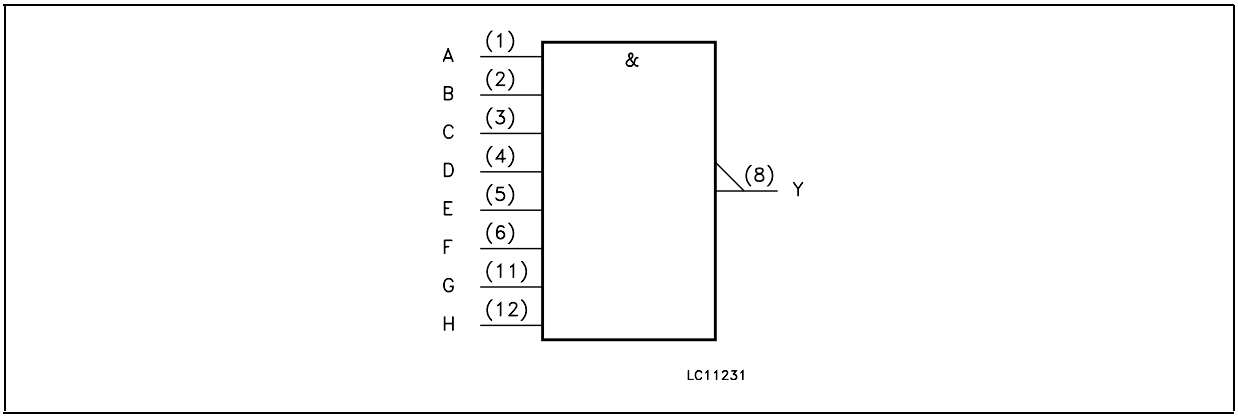
The M54HC30 is an high speed CMOS 8-INPUT NAND GATE fabricated with silicon gate C^2MOS technology.

The internal circuit is composed of 5 stages including buffer output, which enables high noise immunity and stable output.
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

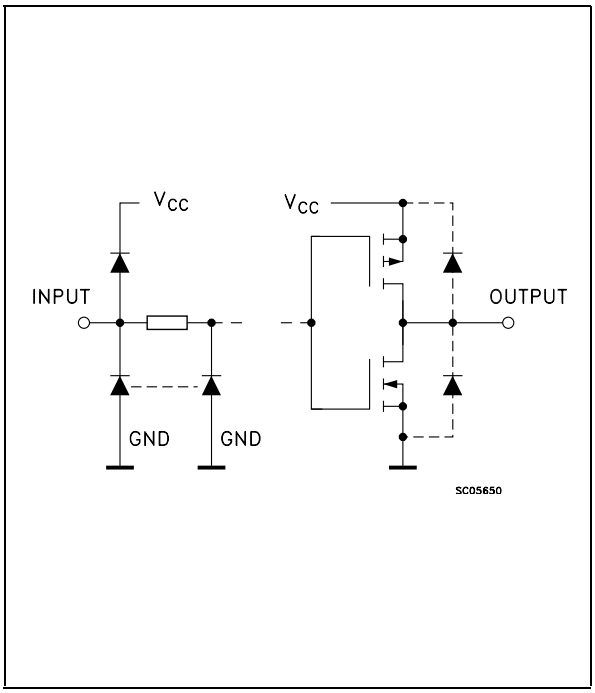
PIN CONNECTION



IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1, 2, 3, 4, 5, 6, 11, 12	A, B, C, D, E, F, G, H,	Data Inputs
9, 10, 13	NC	Not connected
8	Y	Data Output
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	C	D	E	F	G	H	Y
L	X	X	X	X	X	X	X	H
X	L	X	X	X	X	X	X	H
X	X	L	X	X	X	X	X	H
X	X	X	L	X	X	X	X	H
X	X	X	X	L	X	X	X	H
X	X	X	X	X	L	X	X	H
X	X	X	X	X	X	L	X	H
X	X	X	X	X	X	X	L	H
H	H	H	H	H	H	H	H	L

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	300	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	265	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature		-55 to 125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2.0V	0 to 1000	ns
		V_{CC} = 4.5V	0 to 500	ns
		V_{CC} = 6.0V	0 to 400	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5	I_O=-20 µA	4.4	4.5		4.4		4.4		
		6.0	I_O=-20 µA	5.9	6.0		5.9		5.9		
		4.5	I_O=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I_O=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	I_O=20 µA		0.0	0.1		0.1		0.1	V
		4.5	I_O=20 µA		0.0	0.1		0.1		0.1	
		6.0	I_O=20 µA		0.0	0.1		0.1		0.1	
		4.5	I_O=4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I_O=5.2 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND			± 0.1		± 1		± 1	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND			1		10		20	µA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6ns)

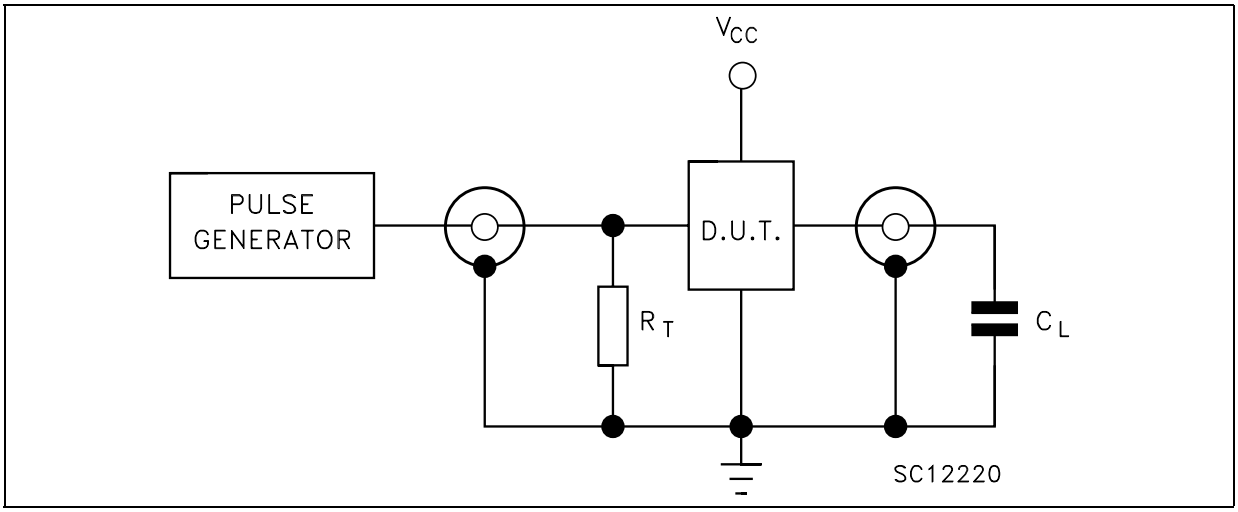
Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time	2.0			45	115		145		170	ns
		4.5			15	23		29		34	
		6.0			13	20		25		29	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C_{IN}	Input Capacitance	5.0			5	10		10		10	pF
C_{PD}	Power Dissipation Capacitance (note 1)	5.0			20						pF

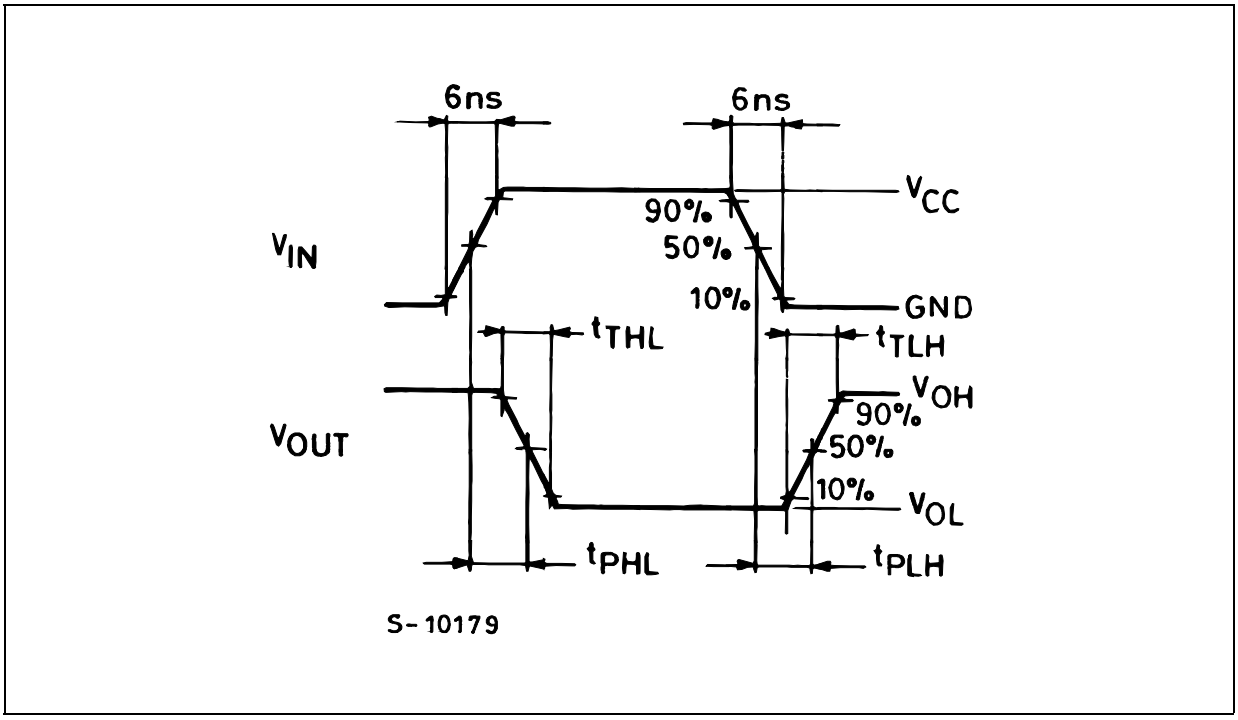
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)}$ = C_{PD} x V_{CC} x f_{IN} + I_{CC}

TEST CIRCUIT



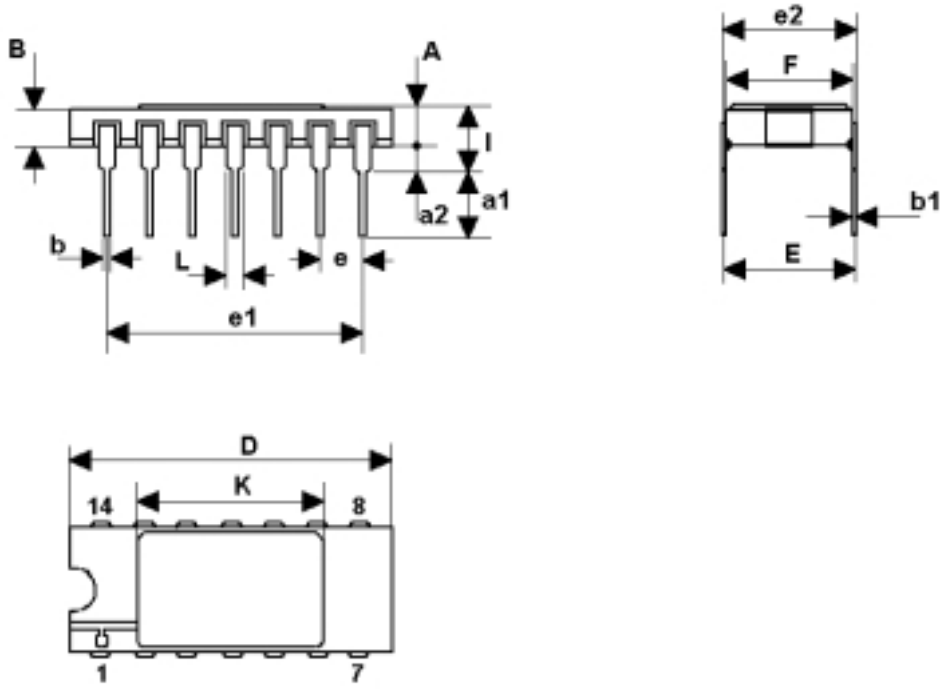
C_L = 50pF or equivalent (includes jig and probe capacitance)
R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



DILC-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.1		22.54	0.083		0.100
a1	3.00		3.70	0.118		0.146
a2	0.63	0.88	1.14	0.025	0.035	0.045
B	1.82	2.03	2.39	0.072	0.080	0.094
b	0.40	0.45	0.50	0.016	0.018	0.020
b1	0.20	0.254	0.30	0.008	0.010	0.012
D	18.79	19.00	19.20	0.740	0.748	0.756
e	7.36	7.62	7.87	0.290	0.300	0.310
e1		2.54			0.100	
e2	15.11	15.24	15.37	0.595	0.600	0.605
e3	7.62	7.87	8.12	0.300	0.310	0.320
F	7.11		7.75	0.280		0.305
I			3.70			0.146
K	10.90		12.1	0.429		0.476
L	1.14	1.27	1.5	0.045	0.050	0.059



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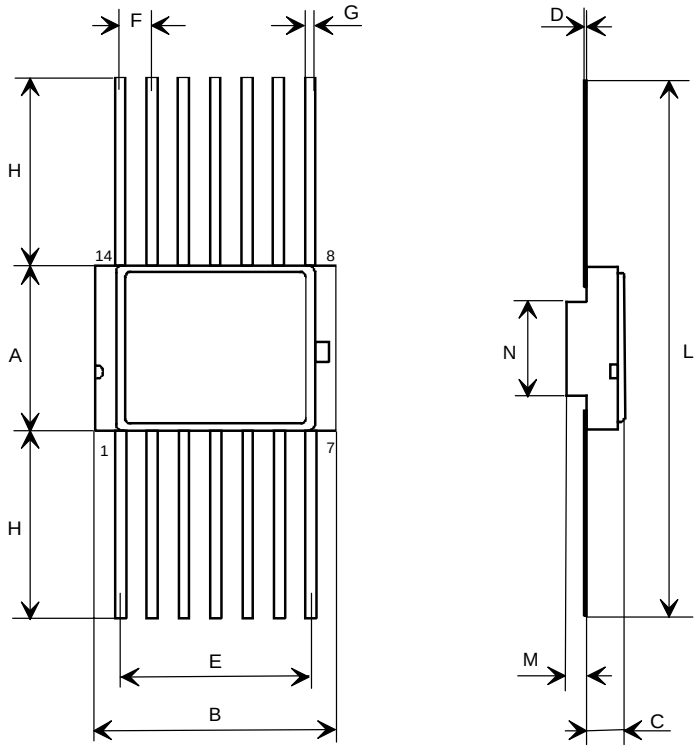
FPC-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	6.75	6.91	7.06	0.266	0.272	0.278
B	9.76	9.95	10.14	0.384	0.392	0.399
C	1.49		1.95	0.059		0.077
D	0.10	0.127	0.15	0.004	0.005	0.006
E	7.50	7.62	7.75	0.295	0.300	0.305
F		1.27			0.050	
G	0.38	0.43	0.48	0.015	0.017	0.019
H		6.0			0.236	
L	18.75		22.0	0.738		0.866
M		0.38			0.015	
N		4.31			0.170	



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